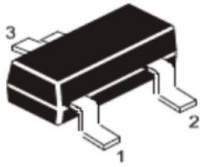
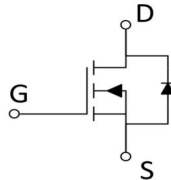


## N CHANNEL STANDARD LEVEL FET

**CDM213SN**  
**SOT-23**  
**Surface Mounted**  
**Plastic Package**



1. GATE  
2. SOURCE  
3. DRAIN



### FEATURES

- Low on-state resistance in a small surface mount package.

### APPLICATIONS

- DC-to-DC primary side switching.

**MARKING CODE : 213**

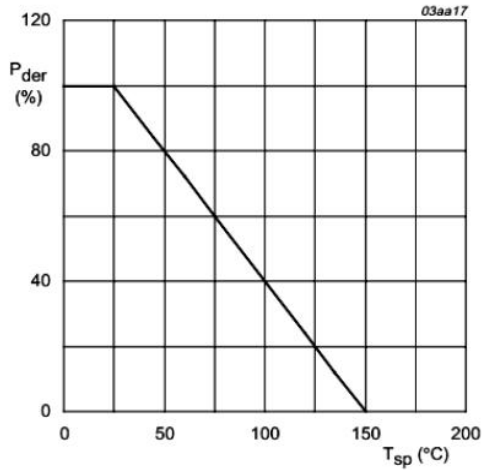
### MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	VALUE	UNIT	
Drain-Source voltage	$V_{DS}$	100	V	
Drain-Gate Voltage	$V_{DGR}$	100		
Gate-Source voltage	$V_{GS}$	$\pm 30$		
Drain Current	$V_{GS}$ at 10 V	$T_{sp} = 25^\circ\text{C}$	1.9	A
		$T_{sp} = 100^\circ\text{C}$	1.2	
Pulsed Drain Current	$I_{DM}$	7.6		
Total Power Dissipation	$P_{tot}$	2	W	
junction temperature	$T_J$	-55 to 150	$^\circ\text{C}$	
storage temperature	$T_{STG}$	-55 to 150	$^\circ\text{C}$	
<b>SOURCE-DRAIN DIODE</b>				
Source (Diode Forward) Current (DC)	$I_S$	1.7	A	
Peak Source (Diode Forward) Current	$I_{SM}$	6.9	A	

**ELECTRICAL CHARACTERISTICS** ( $T_j = 25^\circ\text{C}$  unless otherwise specified)

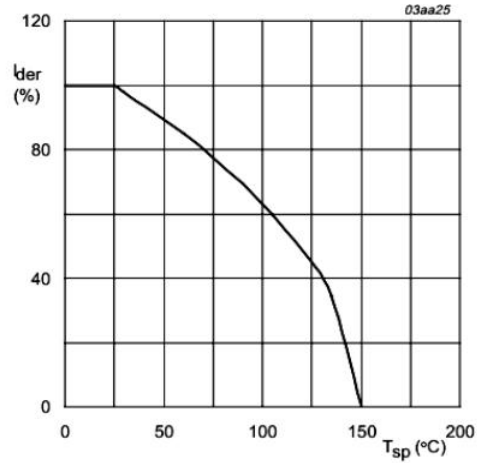
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
<b>STATIC CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	100			V
		$V_{GS}=0V, I_D=250\mu A, T_j=-55^\circ\text{C}$	90			
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=1mA$	1.3	1.8	2.5	V
		$V_{DS}=V_{GS}, I_D=1mA, T_j=150^\circ\text{C}$	1.2			
		$V_{DS}=V_{GS}, I_D=1mA, T_j=-55^\circ\text{C}$			4.4	
Gate-body Leakage current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$		$\pm 10$	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=100V, V_{GS}=0V$			1	$\mu A$
		$V_{DS}=100V, V_{GS}=0V, T_j=150^\circ\text{C}$			100	
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=0.5$		213	250	m $\Omega$
		$V_{GS}=10V, I_D=0.5, T_j=150^\circ\text{C}$		490	575	
<b>DYNAMIC CHARACTERISTICS</b>						
Total Gate Charge	$Q_{g(tot)}$	$V_{GS}=10V, I_D=1.2A, V_{DS}=80V$		7		nC
Gate-Source Charge	$Q_{gs}$			1.4		
Gate-Drain Charge	$Q_{gd}$			2.5		
Input Capacitance	$C_{iss}$	$V_{GS}=0V, V_{DS}=20V, f=1.0MHz$		330		pF
Output Capacitance	$C_{oss}$			36		
Reverse Transfer Capacitance	$C_{rss}$			22		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=50V; R_L=33\Omega; V_{GS}=10V; R_G=6\Omega$		5.5		ns
Rise Time	$t_r$			5		
Turn-Off Delay Time	$t_{d(off)}$			9.5		
Fall Time	$t_f$			3		
<b>SOURCE-DRAIN DIODE</b>						
Diode Forward Voltage	$V_{SD}$	$I_S=1.5A, V_{GS}=0V$		0.83	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_S=1.2A, dI/dt=-100A/\mu s, V_{GS}=0V$		36		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$	$V_{GS}=0V$		23		nC

### CHARACTERISTIC CURVES



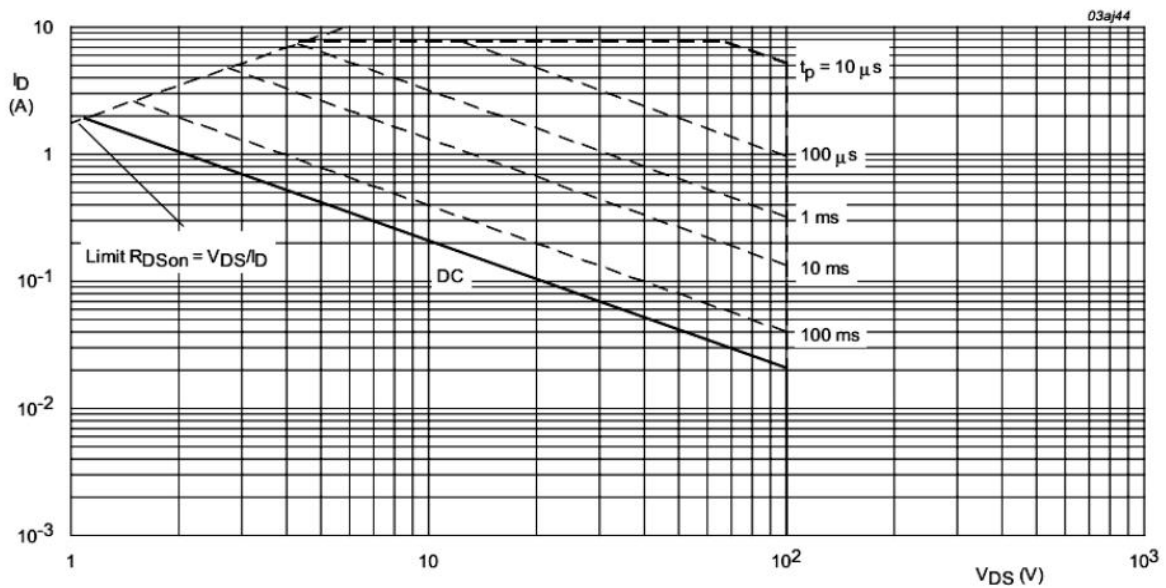
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of solder point temperature.



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of solder point temperature.



$T_{sp} = 25^{\circ}C$ ;  $I_{DM}$  is single pulse;  $V_{GS} = 10V$

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

### CHARACTERISTIC CURVES (Cont..)

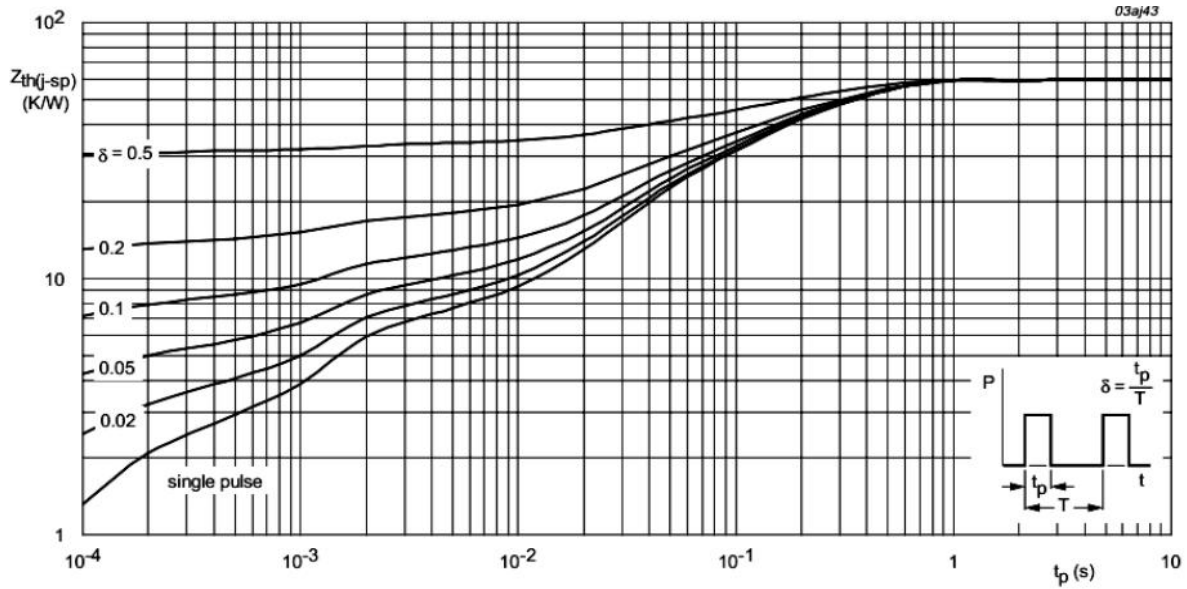


Fig 4. Transient thermal impedance from junction to solder point as a function of pulse duration.

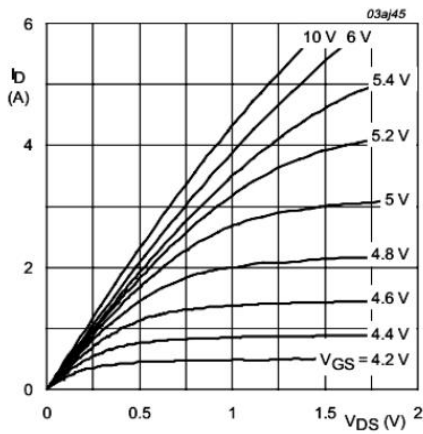


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.

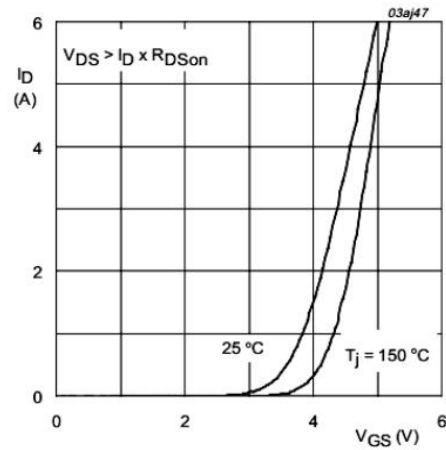
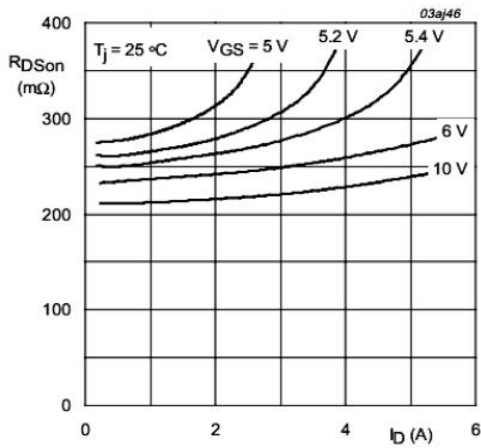


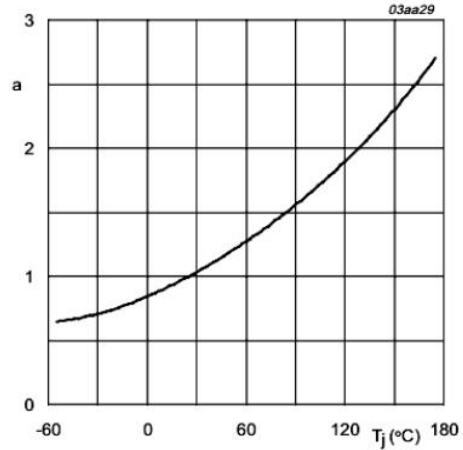
Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values.

### CHARACTERISTIC CURVES (Cont..)



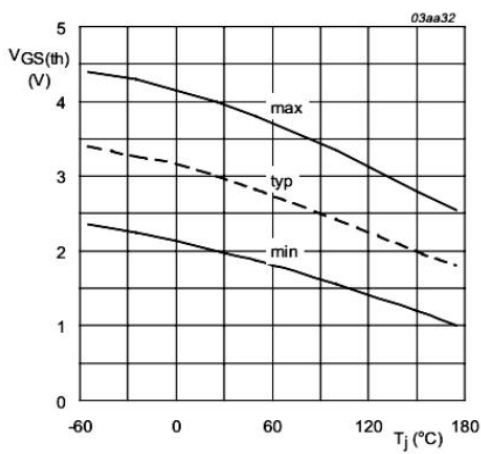
$T_j = 25^\circ\text{C}$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



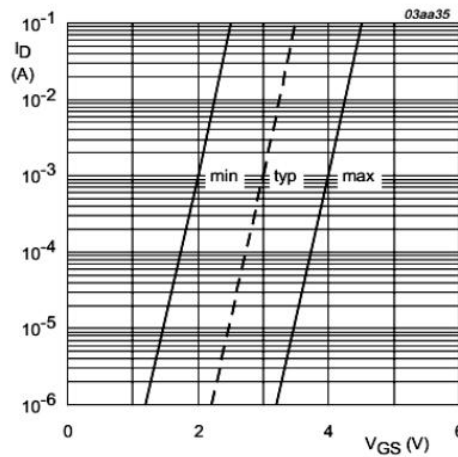
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.



$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

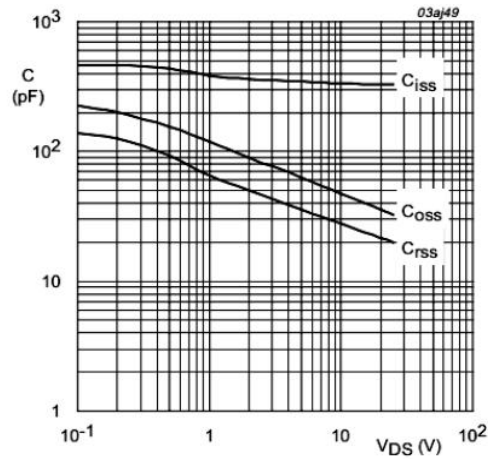
Fig 9. Gate-source threshold voltage as a function of junction temperature.



$T_j = 25^\circ\text{C}$

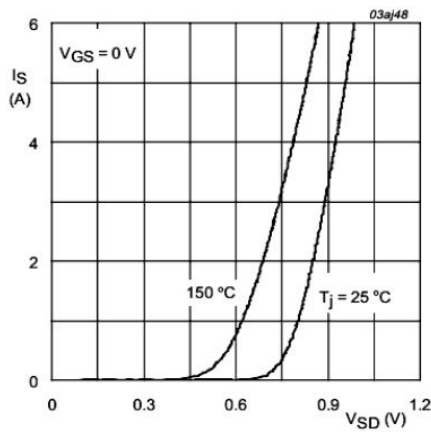
Fig 10. Sub-threshold drain current as a function of gate-source voltage.

### CHARACTERISTIC CURVES (Cont..)



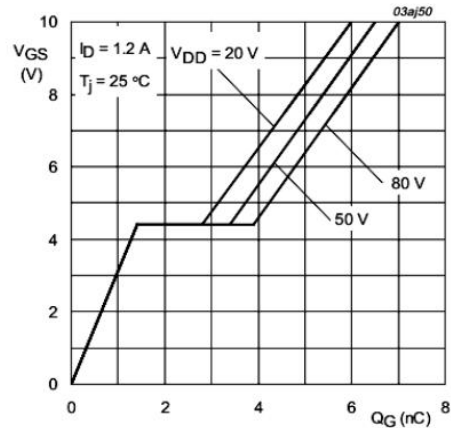
$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 11. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



$T_j = 25\text{ °C}$  and  $150\text{ °C}; V_{GS} = 0\text{ V}$

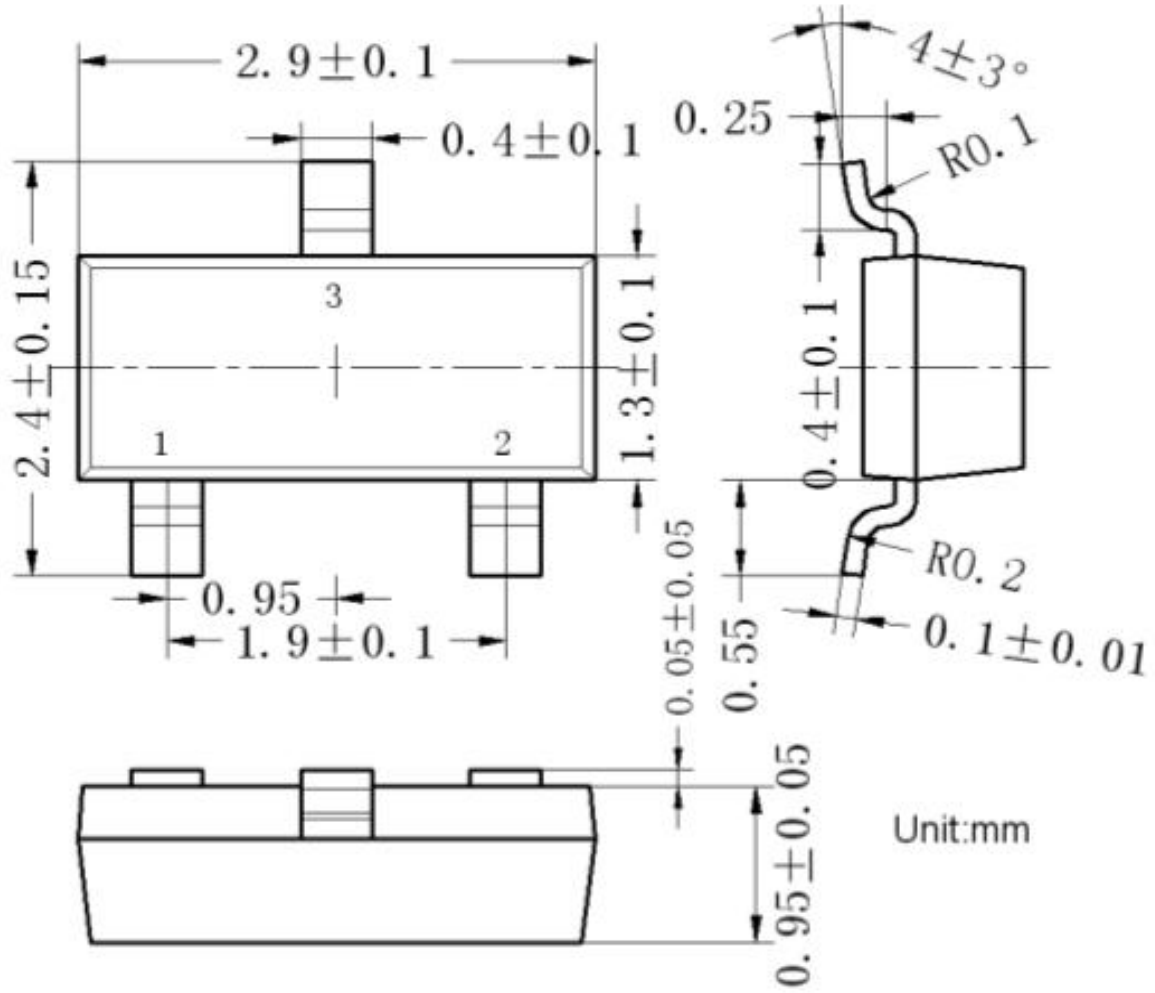
Fig 12. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.



$I_D = 1.2\text{ A}; V_{DD} = 20\text{ V}, 50\text{ V}, 80\text{ V}$

Fig 13. Gate-source voltage as a function of gate charge; typical values.

### SOT-23 PACKAGE DIMENSIONS AND OUTLINE







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2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

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